

QUANTUM NERNST EFFECT IN A BISMUTH SINGLE CRYSTAL

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We report a theoretical calculation explaining the quantum Nernst effect observed experimentally in a bismuth single crystal. Generalizing the edge-current picture in two dimensions, we show that the peaks of the Nernst coefficient survive in three dimensions due to a van Hove singularity. We also evaluate the phonon-drag effect on the Nernst coefficient numerically. Our result agrees with the experimental result for a bismuth single crystal.

Keywords: Bismuth; quantum Hall effect; quantum Nernst effect; phonon-drag effect.

1. Introduction

The Nernst effect is a thermoelectric phenomenon which yields a transverse voltage when there is a magnetic field perpendicular to a temperature gradient. In 2005, Nakamura *et al.*¹ predicted the *quantum* Nernst effect of the two-dimensional electron gas in a semiconductor heterojunction under a strong magnetic field, using the edge current picture of the quantum Hall effect.² In the quantum Nernst effect, the Nernst coefficient shows sharp peaks when a Landau level crosses the

Fermi level and the thermal conductance in the direction of the temperature gradient is quantized. Shirasaki *et al.*³ showed that impurities do not change the conclusions much.

In 2007, Behnia *et al.*^{4,5} have reported quantum oscillation of the Nernst coefficient in a bismuth single crystal, which was similar to the prediction by Nakamura *et al.*¹ It is remarkable that the strong quantum effect is observable in three dimensions; the quantized plateaus of the Hall conductance can be hardly identified in three dimensions.

In the present study we extend the theoretical prediction of the quantum Nernst effect in two dimensions¹ to a three-dimensional system, motivated by the experiment in a bismuth single crystal. We find that the peaks of the Nernst coefficient survive in three dimensions because of a van Hove singularity. A simple calculation explains Behnia *et al.*'s experimental result qualitatively. Consideration of the electron-phonon interaction leads even to quantitative agreement with the experimental result.

2. Edge-current picture of the quantum Nernst effect

We consider the adiabatic Nernst effect. The magnetic field B is applied in the direction of the trigonal axis, which we set to the z axis. The system is electrically and thermally insulated on all surfaces except for the two surfaces attached to heat baths, which induce a temperature bias ΔT in the x direction. Then the Nernst voltage V_N is generated in the y direction. The adiabatic Nernst coefficient is then defined by

$$N = -\frac{V_N/W}{B\Delta T/L}, \quad (1)$$

where L and W are the lengths of the crystal in the x and y directions, respectively.

Nakamura *et al.*¹ assumed that, in a two-dimensional clean sample at low temperatures, an edge current circulates around the system ballistically when the chemical potential is in between two Landau levels. The edge current that departs the colder side maintains the Fermi distribution $f(T_-, \mu_-)$ of the colder bath until it reaches the hotter side and then maintains the Fermi distribution $f(T_+, \mu_+)$ of the hotter bath until it reaches the colder side. The difference of the chemical potential generates the Nernst voltage as $V_N = (\mu_+ - \mu_-)/|e|$.

The Hamiltonian of the two-dimensional electron gas yields energy levels $E(n, k_x)$, where $n = 0, 1, 2, \dots$ represents a Landau

level and the label $-k_m \leq k_x \leq k_m$ represents a state in the Landau level with k_m determined by the confining potential in the y direction. After some algebra they obtained the electric current in the x direction as

$$I = \frac{e}{\pi\hbar} (A_0\Delta\mu + A_1k_B\Delta T), \quad (2)$$

where $\Delta T \equiv T_+ - T_-$, $\Delta\mu \equiv \mu_+ - \mu_-$ and

$$A_\nu(\mu) = \sum_{n=0}^{\infty} \int_{X_0(n)}^{X_1(n)} \frac{x^\nu dx}{4 \cosh^2(x/2)} \quad (3)$$

with $X_i(n) \equiv (E_i(n) - \mu)/(k_B T)$, $E_0(n) \equiv E(n, k_x = 0)$ and $E_1(n) \equiv E(n, k_x = k_m)$. Setting $I = 0$ and $e = |e| > 0$, they obtained the Nernst coefficient as¹

$$N(B, T) = \frac{k_B}{|e|B_z} \frac{L}{W} \frac{A_1}{A_0}, \quad (4)$$

which showed sharp peaks when the chemical potential is equal to a Landau level. This quantum behavior basically comes from the oscillation of the coefficient A_1 .

We now extend the above to three dimensions. This extension introduces an additional argument k_z in the energy level as $E_i(n, k_z) = E_i(n) + (\hbar k_z)^2/(2m_z)$ and hence in $X_i(n, k_z)$. Equation (3) now has integration over k_z as

$$\begin{aligned} \tilde{A}_\nu(\mu) &= \sum_{n=0}^{\infty} \int \frac{dk_z}{2\pi} \int_{X_0(n, k_z)}^{X_1(n, k_z)} \frac{x^\nu dx}{4 \cosh^2(x/2)} \\ &= \int_0^\infty D(E_z) A_\nu(\mu - E_z) dE_z, \end{aligned} \quad (5)$$

where we have changed the integration variable from k_z to $E_z = (\hbar k_z)^2/(2m_z)$. This variable transformation introduces the density of states $D(E_z) \equiv [2\pi(dE_z/dk_z)]^{-1}$, which has a van Hove singularity at $E_z = 0$.

This van Hove singularity is the essence of the survival of the quantum oscillation in three dimensions. The overlap of the peaks of $A_1(\mu)$ with the van Hove singularity leads to oscillatory behavior of the coefficient $\tilde{A}_1(\mu)$ and hence of the Nernst coefficient.

Figure 1 presents the quantum Nernst effect thus obtained in three dimensions. This

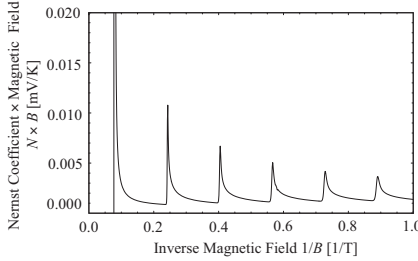


Fig. 1. The Nernst coefficient N times the magnetic field, which is equal to the thermomagnetic power S_{xy} , in three dimensions at $T = 0.28$ K against the inverse magnetic field $1/B$ [1/T], after Eq. (4). We used the following parameter values: the effective mass is $m = 0.06289m_0$ and $m_z = 0.6667m_0$ ⁶ where m_0 is the bare mass of the electron; the size of the Hall bar is $L = 4.0\text{mm}$ ^{4,5} and $W = 2.2\text{mm}$ ^{4,5}; the confining potential at the edges is $V_0 = 4.22$ eV⁷; the chemical potential at equilibrium is $\mu = 11.4\text{meV}$ ⁸.

agrees with the experimental result qualitatively, though the magnitudes of the peaks is much smaller in our calculation than in the experimental result.

3. Phonon-drag effect on the Nernst coefficients

Since the above argument does not quantitatively agree with the experimental result, we now consider the phonon-drag effect. We basically follow Sugihara's theory^{9,10} of the thermoelectric power in bismuth. The difference here is that we treat the Fermi and Bose distribution functions without any approximations and evaluate the magnetic-field dependence of the thermomagnetic power numerically.

The thermomagnetic power $S_{xy} = NB$ is given by

$$S_{xy} = -\frac{Q_y}{TF}\rho_{xx}, \quad (6)$$

where Q_y denotes the heat current in the y direction, F denotes the electric field in the x direction, ρ_{xx} denotes the diagonal resistivity, and we assumed $\rho_{xy} \ll \rho_{xx}$ in bismuth. At low temperatures we may neglect all excitations except acoustic phonons having the

energy $\hbar\omega_q$ and the wave vector $\mathbf{q}$, which are generated through deformation coupling. The heat current in the y direction is then given by

$$Q_y = \int \frac{d\mathbf{q}}{(2\pi)^3} \hbar\omega_q v_s \frac{q_y}{q} (N_q - N_q^{(0)}), \quad (7)$$

where v_s is the group velocity of the phonons. The term $N_q - N_q^{(0)}$ represents the displacement of the phonon distribution N_q from its equilibrium Bose distribution $N_q^{(0)}$.

In order to estimate the displacement, we use the Boltzmann equation in the steady state

$$\left(\frac{\partial N_q}{\partial t}\right)_{\text{carrier}} + \left(\frac{\partial N_q}{\partial t}\right)_{\text{relaxation}} = 0. \quad (8)$$

The first term represents the change of the phonon distribution due to the interaction with carriers and the second term represents that due to other interactions such as boundary scattering, phonon-phonon interaction and impurity scattering. In the steady state these two terms are balanced. In the second term, we assume $(\partial N_q / \partial t)_{\text{relaxation}} = -(N_q - N_q^{(0)}) / \tau_r(q)$ in the relaxation-time approximation; the electron-phonon interaction replaces the phonon distribution, but the relaxation effects make the nonequilibrium phonon distribution to the equilibrium one in time τ_r .

The theoretical result is shown in Fig. 2 (a) and the experimental result is shown in Fig. 2 (b) at three temperatures, respectively. In Fig. 2 (c) we compared the theoretical and experimental result at $T=0.28\text{K}$. The magnitude of the peaks of the theoretical result, after considering the phonon-drag effect, is consistent with the experimental result. Note that there are no adjustable fitting parameters.

4. Summary

We have shown that the quantum Nernst effect survive in three dimensions due to a van

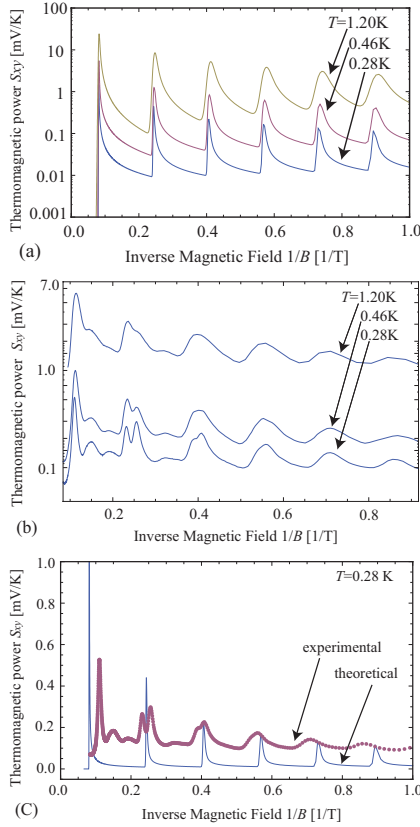


Fig. 2. The thermomagnetic power in three dimensions at $T = 0.28$ K, 0.46 K, 1.20 K against the inverse magnetic field $1/B$ [1/T]: (a) Our theoretical result with the phonon-drag effect; (b) The experimental result by Behnia *et al.*^{4,5}; (c) Comparison of the results at $T = 0.28$ K. In the calculation we used the following parameter values: the deformation potential $D = 1.2\text{eV}^{11}$; the electric resistivity $\rho_{xx} = 0.35\Omega\text{cm}^{4,5}$; the group velocity of the phonons $2 \times 10^3\text{m/s}$; the bismuth density $9.75 \times 10^3\text{kg/m}^3$. The parameter values for the effective mass m and m_z and the chemical potential at equilibrium μ are the same as in Fig. 1.

Hove singularity. We have presented an extension of the edge-current picture in two dimensions to three dimensions, in order to explain Behnia *et al.*'s⁴ experiment for a bismuth single crystal. The naive extension reproduced the quantum oscillation of the experimental result qualitatively. Furthermore, consideration of the phonon-drag effect led us to a theoretical result quantitatively con-

sistent with the experimental result. The peaks are sharper than those in the experiment probably because we neglected impurity scattering of carriers. For simplicity, we also assumed the Fermi surface of bismuth is ellipsoid and considered only the hole contribution. Going beyond these approximations would be an interesting future problem.

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